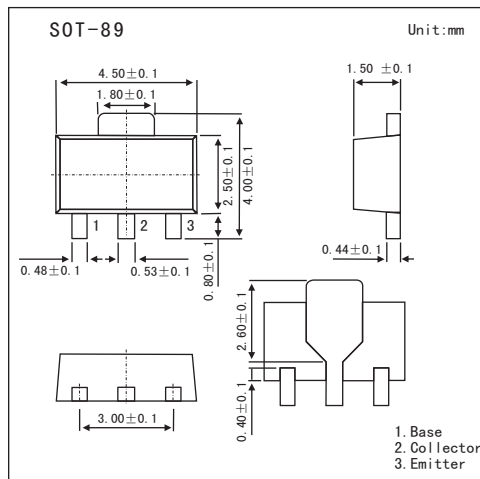


2SC2780

■ Features

- High Collector-emitter voltage.
- Complements to PNP type 2SA1173



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	140	V
Collector-emitter voltage	V _{CEO}	140	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	50	mA
	I _{CP} *1	2.5	A
Collector power dissipation	P _C	0.5	W
	P _C *2	2	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

*1. Pw ≤ 10ms, duty cycle ≤ 50%

*2. When mounted on ceramic substrate of 16cm² × 0.7mm

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CB0}	V _{CB} =140V			0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} =5V			0.1	μA
DC current gain	h _{FE}	V _{CE} =10V, I _C =1mA	50	180		
		V _{CE} =10V, I _C =10mA	90		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =20mA, I _B =2mA		0.07	0.6	V
Base saturation voltage	V _{BE(sat)}	I _C =20mA, I _B =2mA		0.75	1.0	V
Transition frequency	f _T	V _{CE} =10V, I _E =-10mA		120		MHz
Output capacitance	C _{ob}	V _{CB} =10V, I _E =0A, f=1MHz		2.3		pF

■ hFE Classification

Marking	NM	NL	NK
hFE	82~180	120~270	180~390